



# A new irradiation method with a neutron filter for silicon neutron transmutation doping at the Japan research reactor no. 3 (JRR-3)

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## HIGHLIGHTS

- We studied a new silicon irradiation holder with a neutron filter made from B<sub>4</sub>C.
- Designs of the holder were investigated by using the MVP code.
- Calculation method was validated by characteristic experiments in the JRR-3.
- The vertical uniformity was  $\pm 3\%$  when using the new type holder.

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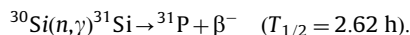
## ABSTRACT

We studied a new silicon irradiation holder with a neutron filter designed to make the vertical neutron flux profile uniform. Since an irradiation holder has to be made of a low activation material, we applied aluminum blended with B<sub>4</sub>C as the holder material. Irradiation methods to achieve uniform flux with a filter are discussed using Monte-Carlo calculation code MVP. Validation of the use of the MVP code for the holder's analyses is also discussed via characteristic experiments.

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## 1. Introduction

Neutron transmutation doping silicon (NTD-Si) (Lark-Horovitz, 1951; Tanenbaum and Mills, 1961) is an n-type doping method carried out by neutron irradiation. The reaction can be described as follows:



This irradiation is carried out mainly in research reactors. The most distinctive feature of NTD-Si is its quite uniform doping. Uniform doping of the entire surface of a silicon ingot is necessary. As the uniformity of doping is higher, the breakdown voltage of the semiconductors is higher (Meese, 1982). Therefore, NTD-Si is used for insulated gate bipolar transistors (IGBTs) of

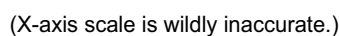
high voltage. There is a growing demand for such IGBTs, because they are effective for energy saving and necessary for infrastructure such as electrical substation equipment and trains.

Most NTD-Si in Japan is produced in the Japan research reactor number 3 (JRR-3) at the Japan Atomic Energy Agency (JAEA). The silicon is cylindrical, with a diameter of 6 in. (15 cm) and a length of 70 cm, including a 10-cm dummy silicon part. The JRR-3 uses holders made from high-purity aluminum (1050) for silicon irradiation. Because the axial flux distribution possesses cosine distribution in the core, particular methods are necessary to achieve uniform irradiation (under  $\pm 8.5\%$ ). There are two methods for making the flux distribution uniform. One method is the so-called reverse method that the JRR-3 has applied. This method is simple and easy to perform, but it requires two irradiation sessions for a silicon ingot to have uniform irradiation along the long axis direction, and a long cooling time of about 2 days is necessary in the interval between the first and second irradiations. In addition, there is low irradiation efficiency because of the

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The purpose of this study was to investigate the possibility of a new holder that does not have restrictions with regard to its mechanical design and filter material. The filter of the new holder



**Fig. 1.** Vertical section image of JRR-3.

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